

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

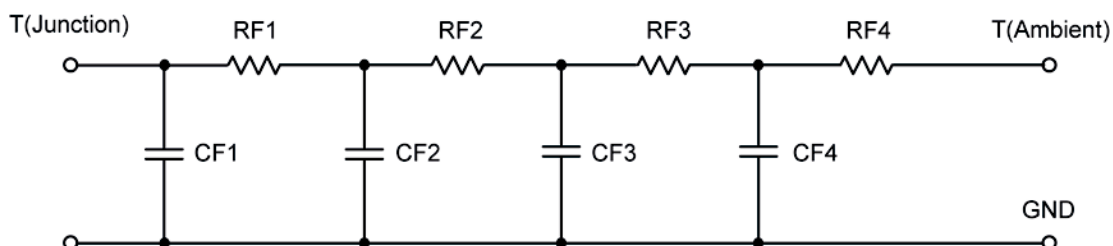
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	24.8736	N/A	28.5067
RT2	6.8016	N/A	15.2315
RT3	70.9289	N/A	33.3805
RT4	47.3959	N/A	2.8813
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	5.8589 m	N/A	11.2005 m
CT2	1.8241 m	N/A	3.9988 m
CT3	14.1363 m	N/A	30.6373 m
CT4	1.6678	N/A	434.1574 u

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	18.1299	N/A	3.7502
RF2	40.2959	N/A	26.0342
RF3	44.5423	N/A	28.9295
RF4	47.0319	N/A	21.2861
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.3357 m	N/A	347.1420 $\mu$
CF2	4.9577 m	N/A	2.1365 m
CF3	10.2156 m	N/A	7.0796 m
CF4	1.5908	N/A	17.1357 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

